

TO SEPARATE, HOLD TOP AND BOTTOM EDGES, SNAP-APART AND DISCARD CARBON

FORM PTO-892
(REV. 2-92)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

SERIAL NO.

09/23,618

GROUP ART UNIT

2823

ATTACHMENT
TO
PAPER
NUMBER

NOTICE OF REFERENCES CITED

APPLICANT(S)

McGAHEY et al.

10821 P.S. PTO
09/24/95
05/07/01

U.S. PATENT DOCUMENTS

*	DOCUMENT NO.	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
A	5391517	2/21/95	GELATOS et al.			
B						
C						
D						
E						
F						
G						
H						
I						
J						
K						

FOREIGN PATENT DOCUMENTS

*	DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUB-CLASS	PERTINENT SHTS. DWG.	PP. SPEC.
L								
M								
N								
O								
P								
Q								

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

R	
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T	
U	

EXAMINER

DATE

DM COLLAS

11/15/00

* A copy of this reference is not being furnished with this office action.
(See Manual of Patent Examining Procedure, section 707.05 (a).)

FORM PTO-1449

INFORMATION DISCLOSURE CITATIONAtty Docket
FI9-98-172Serial No.
09/231,618Applicant
Ivers et alFiling Date
January 14, 1999Group Art U
1773JCE21 U.S. PTO
09/849530**U.S. PATENT DOCUMENTS**

Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date
Dnc	AA	3,765,956	10/73	Li	148	33	
	AB	5,324,684	6/94	Kermani et al	437	95	
	AC	5,447,887	9/95	Filipiak et al	437	200	
	AD	5,489,550	2/96	Moslehi	437	165	
	AE	5,529,954	6/96	Iijima et al	437	189	
↓	AF	5,633,047	5/97	Brady et al	427	437	
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Sub-Class	Translation
	AL						Yes No
	AM						Yes No
	AN						Yes No
	AO						Yes No
	AP						Yes No

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

Dnc	AR		Chemical Vapor Deposition of Cu ₃ Ge for High Aspect Ratio Metallization, <i>IBM Technical Disclosure Bulletin</i> 35, No. 4B, September 1992.
↓	AS		Aboelfotoh et al, Copper Passivation of Boron in Silicon and Boron Reactivation Kinetics, <i>Physical Review B</i> 44, No. 23, December 15, 1991.
↓	AT		Liou et al, Oxidation of Cu and Cu ₃ Ge Thin Films, <i>J. Appl. Phys.</i> 77, No. 10, May 1995.

Examiner

D. M. COLLETS

Date Considered

11/16/00

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609.
 Draw line through citation if not in conformance and not considered.
 Include copy of this form with next communication to Applicant.

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

FI9-98-17

Application Number

09/231,618

Applicant(s)

T. H. Ivers, et al.

Filing Date

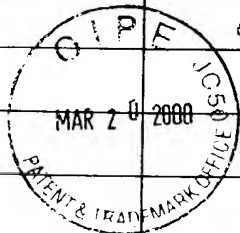
01/14/99

Group Art Unit

1773

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Dne		5,855,993	01/05/99	Brady, et al.			



FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
Dne		0 472 804 A2	04/03/92	Europe				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

D. H. Courts

DATE CONSIDERED

11-16-00

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1773**U.S. PATENT DOCUMENTS**

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Dm	AA	3,765,956	10/73	Li	148	33	
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	AM						Yes No
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Dm	AR		Chemical Vapor Deposition of Cu ₃ Ge for High Aspect Ratio Metallization, <i>IBM Technical Disclosure Bulletin</i> 35, No. 4B, September 1992.
	AS		Aboelfotoh et al, Copper Passivation of Boron in Silicon and Boron Reactivation Kinetics, <i>Physical Review B</i> 44, No. 23, December 15, 1991.
	AT		Liou et al, Oxidation of Cu and Cu ₃ Ge Thin Films, <i>J. Appl. Phys.</i> 77, No. 10, May 1995.

Examiner

D, M. Collins

Date Considered

10-29-01

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